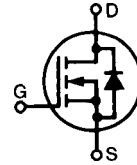


HiPerFET™ Power MOSFETs

IXFH/IXFM15N60
IXFH/IXFM20N60

N-Channel Enhancement Mode
High dv/dt, Low t_{rr} , HDMOS™ Family

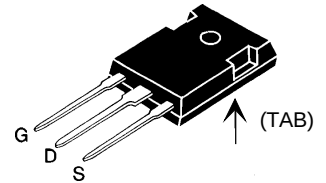


V_{DSS}	I_{D25}	$R_{DS(on)}$
600 V	15 A	0.50 Ω
600 V	20 A	0.35 Ω

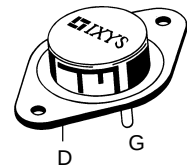
$t_{rr} \leq 250$ ns

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ M Ω	600	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	15N60 20N60	15 20 A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	15N60 20N60	60 80 A
I_{AR}	$T_C = 25^\circ\text{C}$	15N60 20N60	15 20 A
E_{AR}	$T_C = 25^\circ\text{C}$	30	mJ
dv/dt	$I_S \leq I_{DM}$, di/dt ≤ 100 A/ μ s, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		TO-204 = 18 g, TO-247 = 6 g	

TO-247 AD (IXFH)



TO-204 AE (IXFM)



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

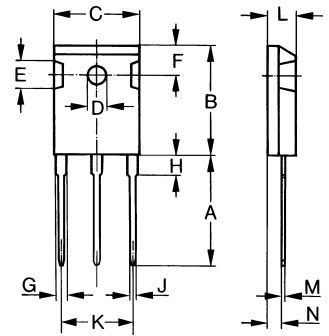
Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

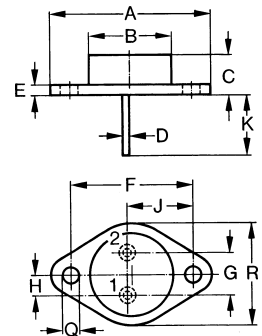
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 250$ μ A	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4$ mA	2.0		4.5 V
I_{GSS}	$V_{GS} = \pm 20$ V, $V_{DS} = 0$			± 100 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$, $V_{GS} = 0$ V			250 μ A 1 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 0.5 \cdot I_{D25}$	15N60 20N60		0.50 Ω 0.35 Ω
Pulse test, $t \leq 300$ μ s, duty cycle $d \leq 2$ %				

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	11	18	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4500	pF
C_{oss}			420	pF
C_{rss}			140	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2\ \Omega$ (External)		20	40 ns
t_r			43	60 ns
$t_{d(off)}$			70	90 ns
t_f			40	60 ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		151	170 nC
Q_{gs}			29	40 nC
Q_{gd}			60	85 nC
R_{thJC}			0.25	0.42 K/W
R_{thCK}				K/W

Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$	15N60 20N60		15 A 20 A
I_{SM}	Repetitive; pulse width limited by T_{JM}	15N60 20N60		60 A 80 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V},$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = I_S$ $-di/dt = 100\text{ A}/\mu\text{s},$ $V_R = 100\text{ V}$	$T_J = 25^\circ\text{C}$		250 ns
		$T_J = 125^\circ\text{C}$		400 ns
Q_{RM}		$T_J = 25^\circ\text{C}$		1 μC
		$T_J = 125^\circ\text{C}$		2 μC
I_{RM}		$T_J = 25^\circ\text{C}$		10 A
		$T_J = 125^\circ\text{C}$		15 A

TO-247 AD (IXFH) Outline


Dim.	Millimeter Min. Max.	Inches Min. Max.
A	19.81 20.32	0.780 0.800
B	20.80 21.46	0.819 0.845
C	15.75 16.26	0.610 0.640
D	3.55 3.65	0.140 0.144
E	4.32 5.49	0.170 0.216
F	5.4 6.2	0.212 0.244
G	1.65 2.13	0.065 0.084
H	- 4.5	- 0.177
J	1.0 1.4	0.040 0.055
K	10.8 11.0	0.426 0.433
L	4.7 5.3	0.185 0.209
M	0.4 0.8	0.016 0.031
N	1.5 2.49	0.087 0.102

TO-204 AE (IXFM) Outline


Dim.	Millimeter Min. Max.	Inches Min. Max.
A	38.61 39.12	1.520 1.540
B	- 22.22	- 0.875
C	6.40 11.40	0.252 0.449
D	1.45 1.60	0.057 0.063
E	1.52 3.43	0.060 0.135
F	30.15 BSC	1.187 BSC
G	10.67 11.17	0.420 0.440
H	5.21 5.71	0.205 0.225
J	16.64 17.14	0.655 0.675
K	11.18 12.19	0.440 0.480
Q	3.84 4.19	0.151 0.165
R	25.16 26.66	0.991 1.050

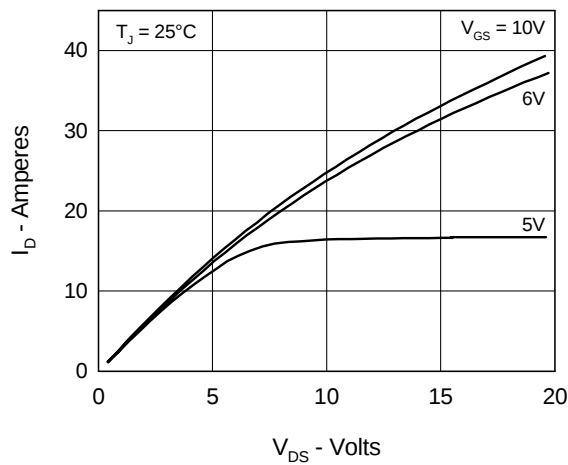
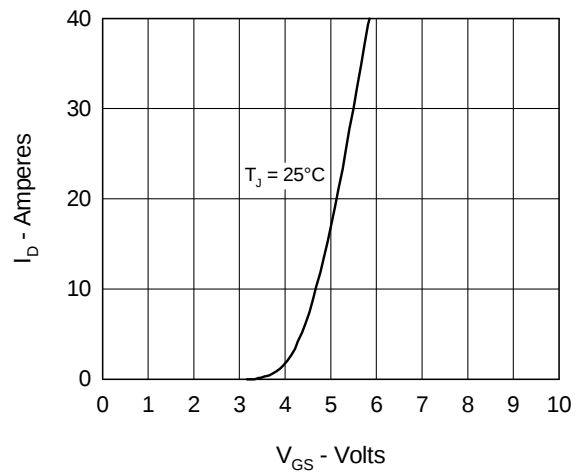
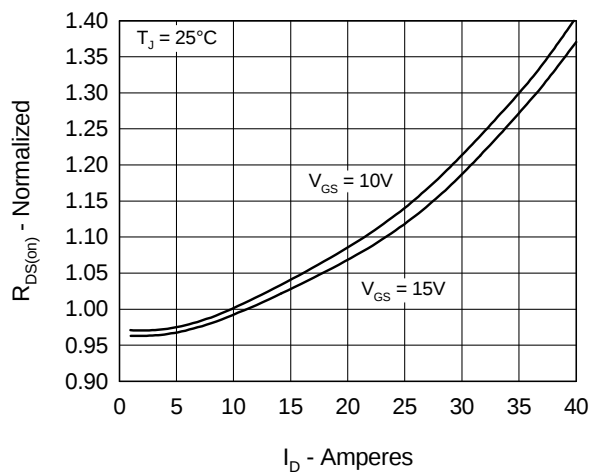
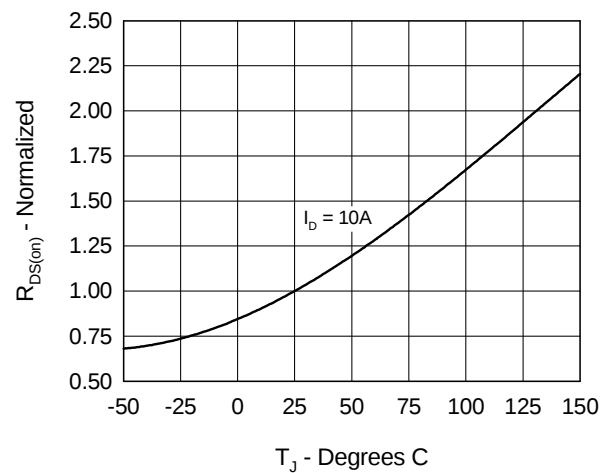
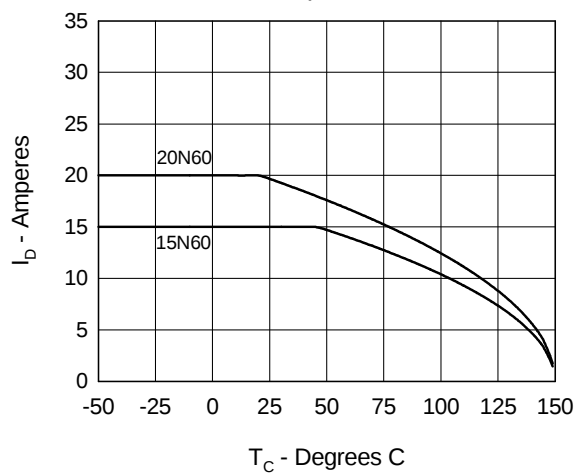
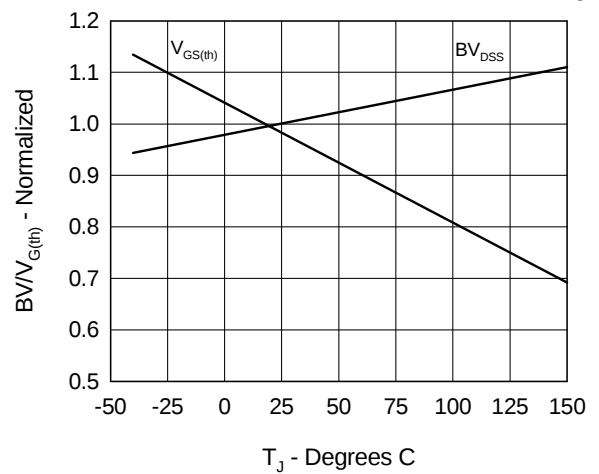
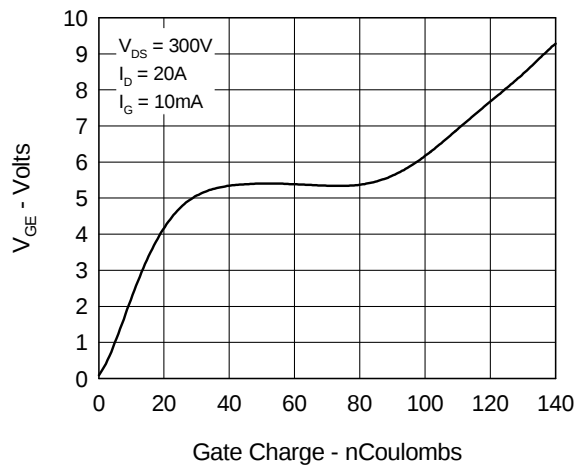
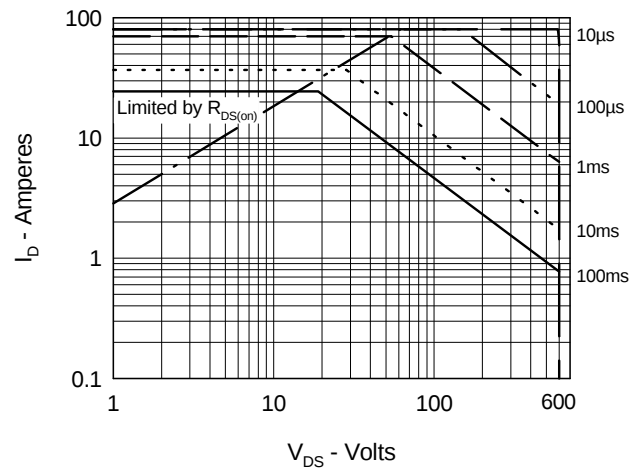
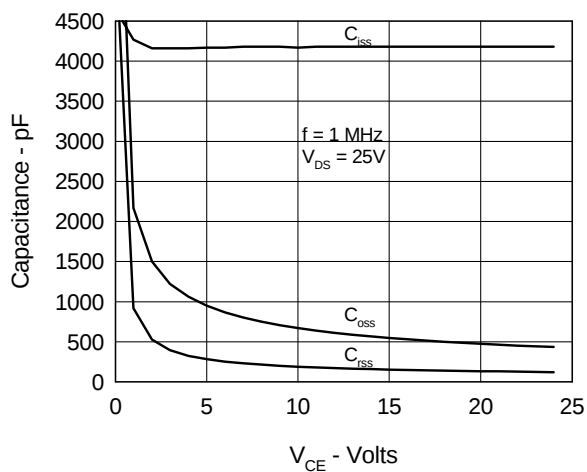
Fig. 1 Output Characteristics

Fig. 2 Input Admittance

Fig. 3 $R_{DS(on)}$ vs. Drain Current

Fig. 4 Temperature Dependence of Drain to Source Resistance

Fig. 5 Drain Current vs. Case Temperature

Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage


Fig.7 Gate Charge Characteristic Curve

Fig.8 Forward Bias Safe Operating Area

Fig.9 Capacitance Curves

Fig.10 Transient Thermal Impedance
